

Wafer Level Microwave Plasma Treatment CL1000M

High Density Plasma Treatment
ESD-FREE Solution for Ring Wafer



Diverse microwave plasma applications for surface treatment

- Surface cleaning and activation prior to wire bonding or molding
- Plasma de-smear and de-flash process for EMC residues removal
- Redox solution for oxidized metal surface

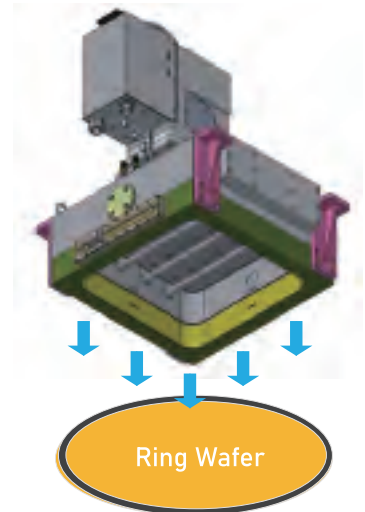
High uniformity performance without ESD

- Rotary chuck design to enhance uniformity, CPK > 1.67
- Microwave plasma to achieve ESD-FREE solution

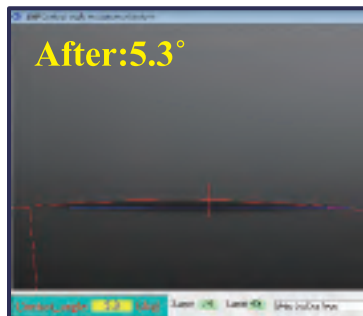
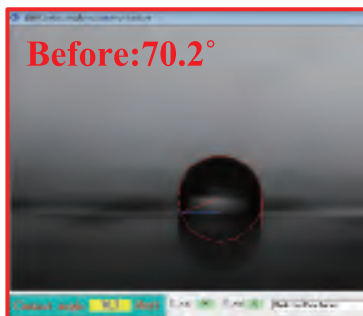
Fully automated design for 6"/8"/12" ring wafer

- Stable robot arm handling system
- Special chuck table design to adapt various dimension products

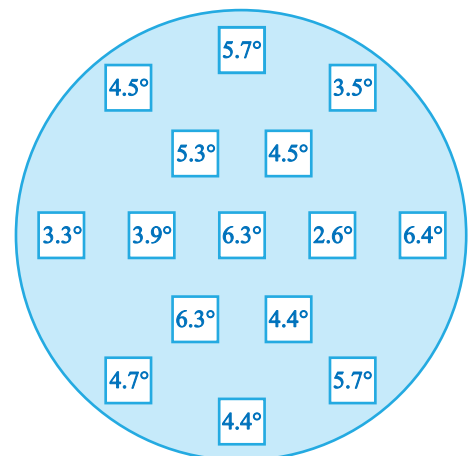
Plasma Array Design



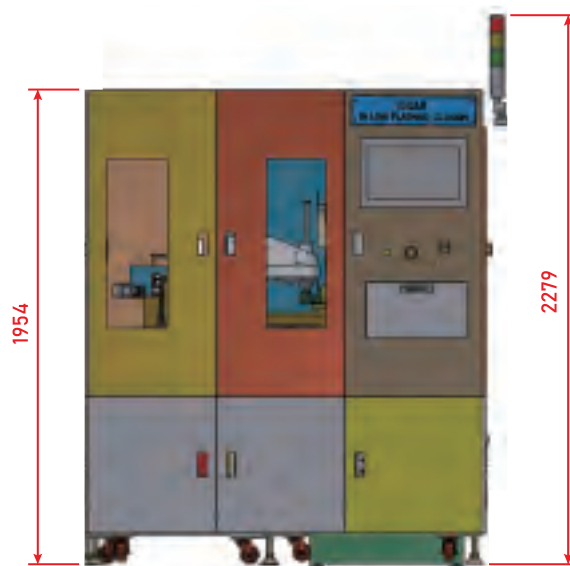
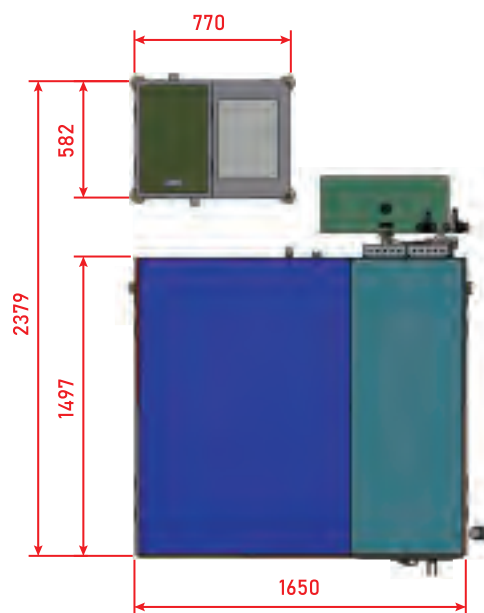
Contact Angle Result



Perfect contact angle and uniformity result

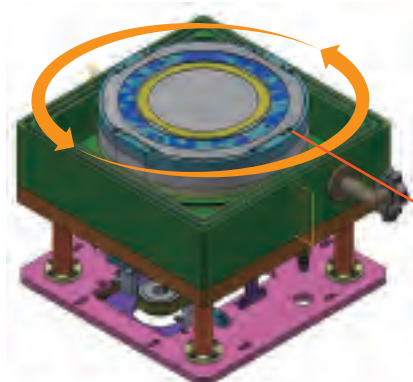


Machine Layout



Chuck Design

Rotary chuck for high uniformity achievement



Rotary Chuck

Water cooling plate for ring tape protection



Specification

Plasma Source	MW 2KW, 2.45GHz
Process Gas	Ar/O ₂ /N ₂ /CF ₄
Product Size	6"/8"/12" Ring wafer
Process Temperature	40 – 70 °C
Process Pressure	0.05 – 1 Torr
Base Pressure	< 0.03 Torr
Chuck Design	Rotary chuck with cooling plate
WPH	40 pcs/ Plasma @ 15 Secs

